

MICROCIRCUIT DATA SHEET

MNLM2940-12-X REV 1A1

Original Creation Date: 07/22/96 Last Update Date: 10/08/99 Last Major Revision Date: 07/22/96

1A LOW DROPOUT REGULATOR

General Description

The LM2940 positive voltage regulator features the ability to source 1A of ouput current with a dropout voltage of typically 0.5V and a maximum of 1V over the entire temperature range. Furthermore, a quiescent current reduction circuit has been included which reduces the ground current when the differential between the input voltage and the output voltage exceeds approximately 3V. The quiescent current with 1A of output current and an input-output differential of 5V is therefore only 30 mA. Higher quiescent currents only exist when the regulator is in the dropout mode (Vin - Vout \leq 3V).

Designed also for vehicular applications, the LM2940 and all regulated circuitry are protected from reverse battery installations, the LM2940 and all regulated circuity are protected from reverse battery installations or 2-battery jumps. During line transients, such as load dump when the input voltage can momentarily exceed the specified maximum operating voltage, the regulator will automaically shut down to protect both the internal circuits and the load. The LM2940 cannot be harmed by temporary mirror-image insertion. Familiar regulator features such as short circuit and thermal overload protection are also provided. 次茂

Industry Part Number	NS Part Numbers
LM2940	LM2940J-12/883 LM2940K-12/883 LM2940WG-12/883
Prime Die	In2)40WG-12/003
LM2940	
Controlling Document	
SEE FEATURE SECTION	

Processing

MIL-STD-883, Method 5004

Quality Conformance Inspection

MIL-STD-883, Method 5005

Subgrp	Description	Temp	(°C)
1 2 3 4 5 6 7 8A 8B 9 10 11	Static tests at Static tests at Static tests at Dynamic tests at Dynamic tests at Functional tests at Functional tests at Functional tests at Switching tests at Switching tests at	+25 +125 -55 +25 +125 +25 +125 -55 +25 +125 +125 -55	

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Features

- Dropout voltage typically 0.5V @ Io = 1A
- Output current in excess of 1A
- Output voltage trimmed before assembly
- Reverse battery protection
- Internal short circuit current limit
- Mirror image insertion protection
- CONTROLLING DOCUMENT
- LM2940J-12/883 5962-9088401QEA
- LM2940K-12/883 5962-9088401MYA
- LM2940WG-12/883

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(Absolute Maximum Ratings)

(Note 1)

Input Voltage (Survival Voltage <100ms) 60V Internal Power Dissipation (Note 2, 3) Internally Limited Maximum Junction Temperature 150 C Storage Temperature Range -65 C to +150 C Lead Temperature (Soldering, 10 seconds) 300 C Thermal Resistance ThetaJA T03 Pkg T03 Pkg (Still Air) 40 C/W (500LF/Min Air flow) TBD (Still Air) CERDIP 73 CERDIP (500LF/Min Air flow) ·爱·芬 CERAMIC SOIC (Still Air) CERAMIC SOIC (500LF/Min Air Flow) C ThetaJC т03 CERDIP (Note 3) CERAMIC SOIC 5 C/W (Note 3) Package Weight (Typcial) T03 Pkg TBD 1970ma CERDIP CERAMIC SOIC 360mg ESD Susceptibility (Note 4)4000V

- Absolute Maximum Ratings are limits beyond which damage to the device may occur. Note 1: Operating Ratings are conditions for which the device is functional, but do not guaranteed specific performance limits. For guaranteed specifications and test conditions see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions. The maximum power dissipation must be derated at elevated temperatures and is
- Note 2: dictated by Tjmax (maximum junction temperature), ThetaJA (package junction to ambient thermal resistance), and TA (ambient temperature). The maximum allowable power dissipation at any temperature is Pdmax = (Tjmax - TA)/ThetaJA or the number given in the Absolute Maximum Ratings, whichever is lower.
- Note 3: The package material for these devices allows much improved heat transfer over our standard ceramic packages. In order to take full advantage of this improved heat transfer, heat sinking must be provided between the package base (directly beneath the die), and either metal traces on, or thermal vias through, the printed circuit board. Without this additional heat sinking, device power dissipation must be calculated using junction-to-ambient, rather than junction-to-case, thermal resistance. It must not be assumed that the device leads will provide substantial heat transfer out of the package, since the thermal resistance of the leadframe material is very poor, relative to the material of the package base. The stated junction-to-case thermal resistance is for the package material only, and does not account for the additional thermal resistance between the package base and the printed circuit board. The user must determine the value of the additional thermal $\dot{\mathsf{r}}$ resistance and must combine this with the stated value for the package, to calculate the total allowed power dissipation for the device. Human body model, 100pF discharged through 1.5K Ohms
- Note 4:

Recommended Operating Conditions

(Note 1)

Input Voltage

Operating Temperature Range

26V

-55 C \leq TA \leq +125 C

Note 1: Absolute Maximum Ratings are limits beyond which damage to the device may occur. Operating Ratings are conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.



Electrical Characteristics

DC PARAMETERS:

(The following conditions apply to all the following parameters, unless otherwise specified.) DC: Vin = 17V, Io = 1A, Cout = 22 u F

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN- NAME	MIN	MAX	UNIT	SUB- GROUPS
Vout	Output Voltage	Vin = 17V, Io = 5mA			11.64	12.36	V	1
					11.40	12.60	V	2, 3
		Vin = 13.6V, Io = 5mA			11.64	12.36	V	1
					11.40	12.60	V	2, 3
		Vin = 14V, Io = 5mA			11.64	12.36	V	1
			37	5	11.40	12.60	V	2, 3
		Vin = 26V, Io = 5mA	-	1	11.64	12.36	V	1
		30 3 T2		-	11.40	12.60	V	2, 3
		Vin = 14V, Io = 5mA Vin = 26V, Io = 5mA Vin = 17V, Io = 1A			11.64	12.36	V	1
					11.40	12.60	V	2, 3
		Vin = 13.6V, IO = 1A			11.64	12.36	V	1
					11.40	12.60	V	2, 3
		Vin = 13.6V, Io = 50mA			11.64	12.36	V	1
					11.40	12.60	V	2, 3
		Vin = 17V, Io = 50mA			11.64	12.36	V	1
					11.40	12.60	V	2, 3
	Reverse Polarity Input Voltage DC	Ro = 100 Ohms	1		-15		V	1, 2, 3
Iq	Quiescent Current	Vin = 17V, Io = 5mA			0	15	mA	1
					0	20	mA	2, 3
		Vin = 14V, Io = 5mA			0	15	mA	1
					0	20	mA	2, 3
		Vin = 26V, Io = 5mA			0	15	mA	1
					0	20	mA	2, 3
		Vin = 17V, Io = 1A			0	50	mA	1
					0	60	mA	2, 3
Vrline	Line Regulation	$14V \leq Vin \leq 26V$, Io = 5mA			-75	75	mV	1
					-120	120	mV	2, 3
Vrload	Load Regulation	Vin = 17V, 50mA \leq Io \leq 1A			-120	120	mV	1
					-190	190	mV	2, 3

Electrical Characteristics

DC PARAMETERS: (Continued)

(The following conditions apply to all the following parameters, unless otherwise specified.) DC: Vin = 17V, Io = 1A, Cout = 22 u F

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN- NAME	MIN	MAX	UNIT	SUB- GROUPS
Vdo	Dropout Voltage	Io = 1A			0	0.7	V	1
					0	1	V	2, 3
		Io = 100mA			0	200	mV	1
					0	300	mV	2, 3
Isc	Short Circuit Current	Vin = 17V			1.6		A	1
	current		37	5	1.3		A	2, 3
AC PAR	AMETERS:	3	C	5				·

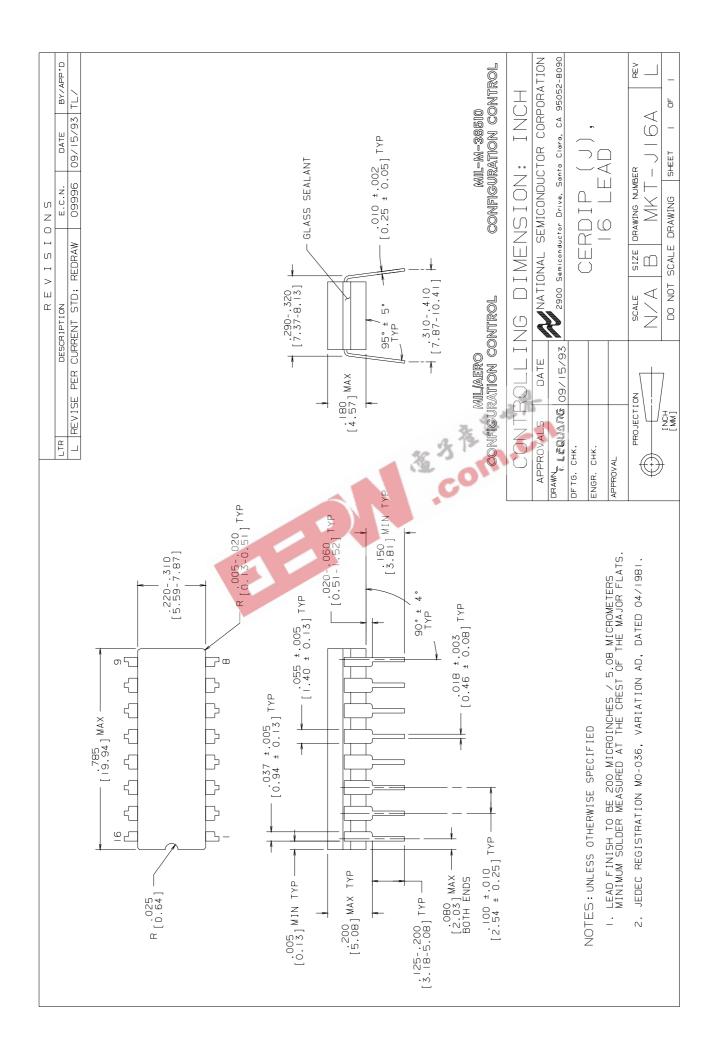
(The following conditions apply to all the following parameters, unless otherwise specified.) AC: Vin = 17V, Io = 1A, Cout = 22uF

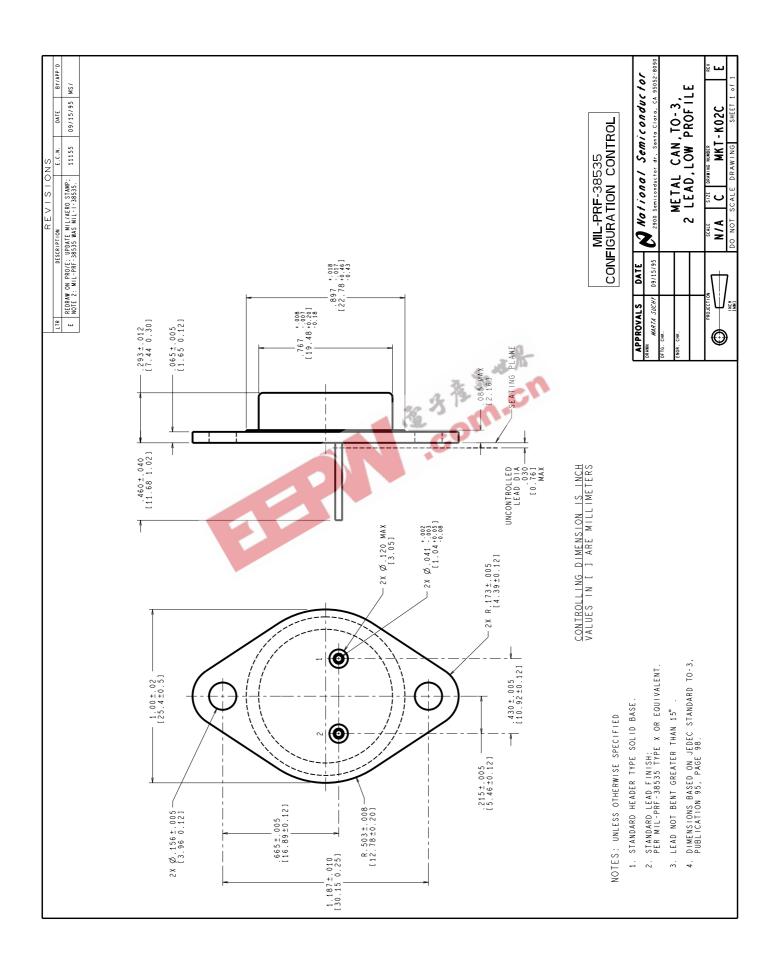
	Max Line Transient	$Vo \leq 13V$, Ro = 100 Ohms, T = 20ms	1	40		V	7, 8A, 8B
	Reverse Polarity Input Voltage Transient	T = 20ms, Ro = 100 Ohms	1	-45		V	7, 8A, 8B
No	Output Noise Voltage	Vin = 17V, Io = 5mA, 10Hz = 100KHz	1	0	1000	uVrms	;4,5, 6
Zo	Output Impedance	Vin = $17V$, Io = $100mA$ DC and $20mA$ AC, fo = $120Hz$	1		1	Ohm	4, 5, 6
RR	Ripple Rejection	Vin = $17V$, $1Vrms$, f = $1KHz$, Io = $5mA$	1	52		dB	4
			1	46		dB	5,6

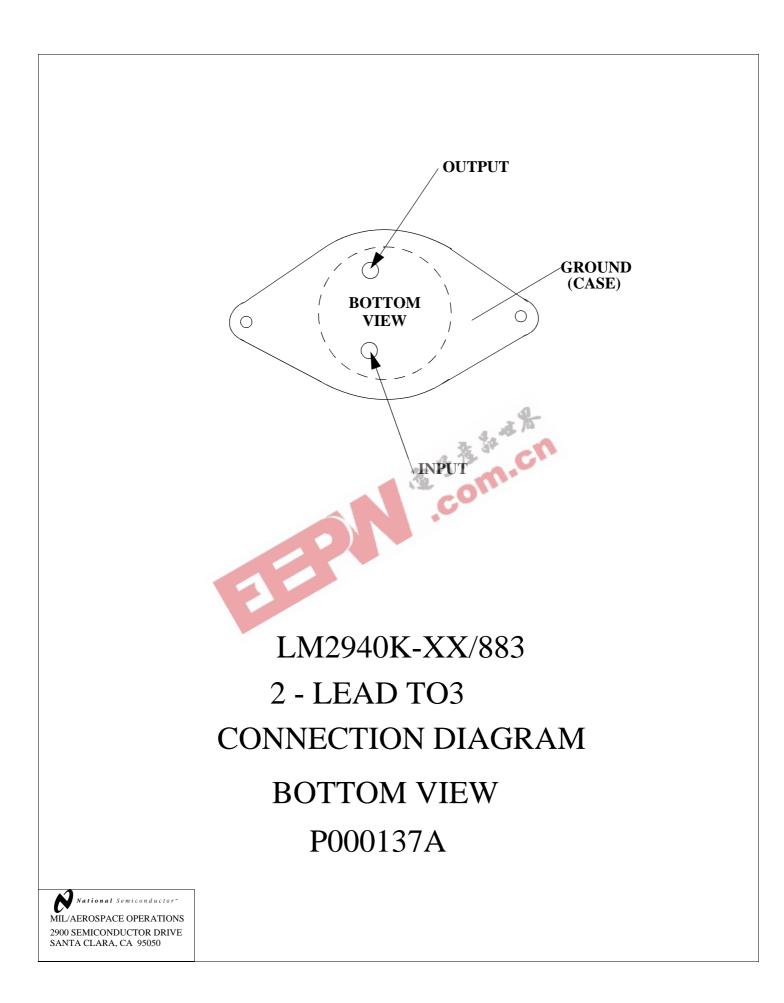
Note 1: Functional test only.

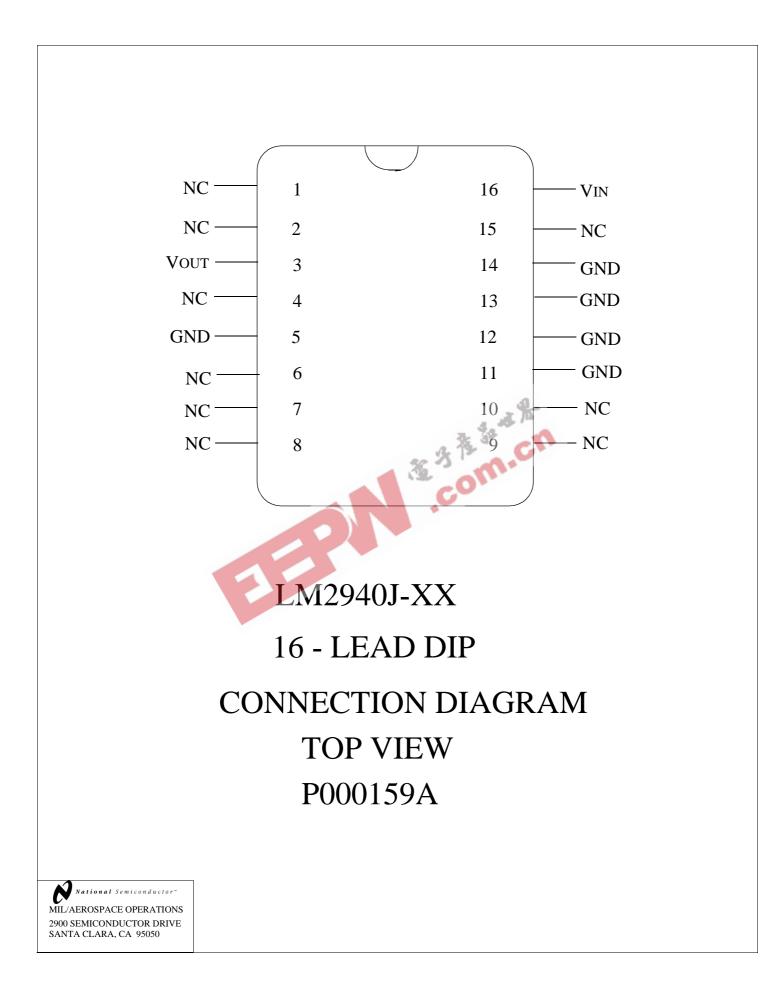
Graphics and Diagrams

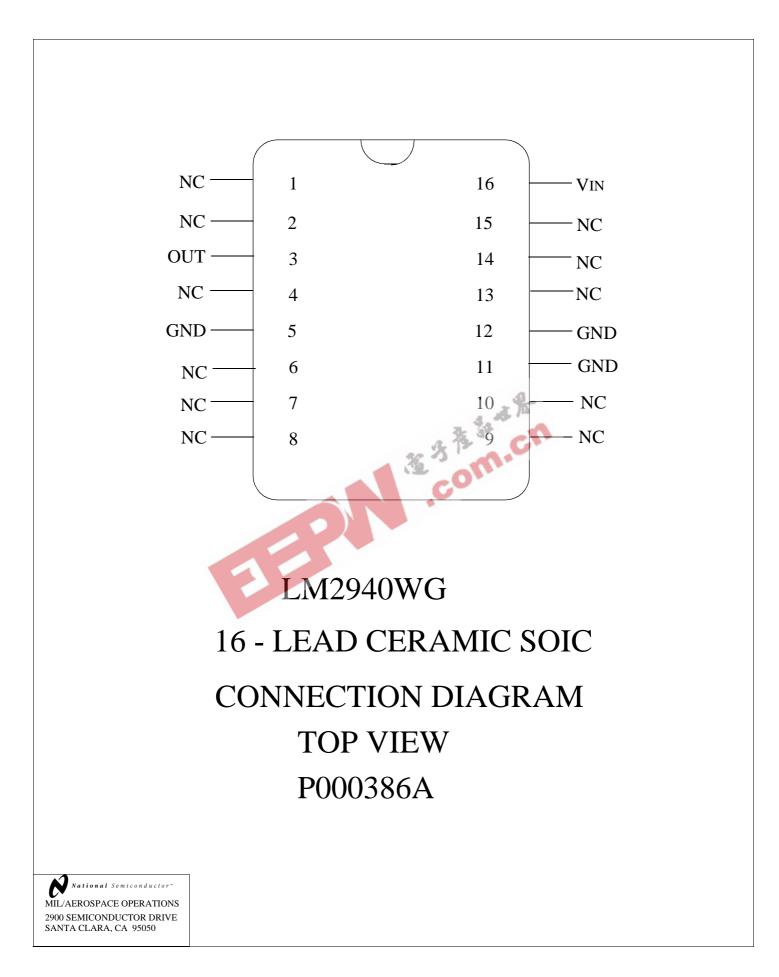
GRAPHICS#	DESCRIPTION			
05826HRA2	METAL CAN (KA), TO-3, 2LD, LOW PROFILE (B/I CKT)			
06332HRA2	CERDIP (J), 16 LEAD (B/I CKT)			
06351HRA1	ERPACK (W), 16 LEAD (B/I CKT)			
J16ARL	ERDIP (J), 16 LEAD (P/P DWG)			
K02CRE	METAL CAN (KA), TO-3, 2LD, LOW PROFILE (P/P DWG)			
P000137A	METAL CAN (KA), TO-3, 2LD, LOW PROFILE (PINOUT)			
P000159A	CERDIP (J), 16 LEAD (PINOUT)			
P000386A	CERAMIC SOIC (WG), 16 LEAD (PINOUT)			
WG16ARC	CERAMIC SOIC (WG), 16 LEAD (P/P DWG)			
See attached graphics following this page.				

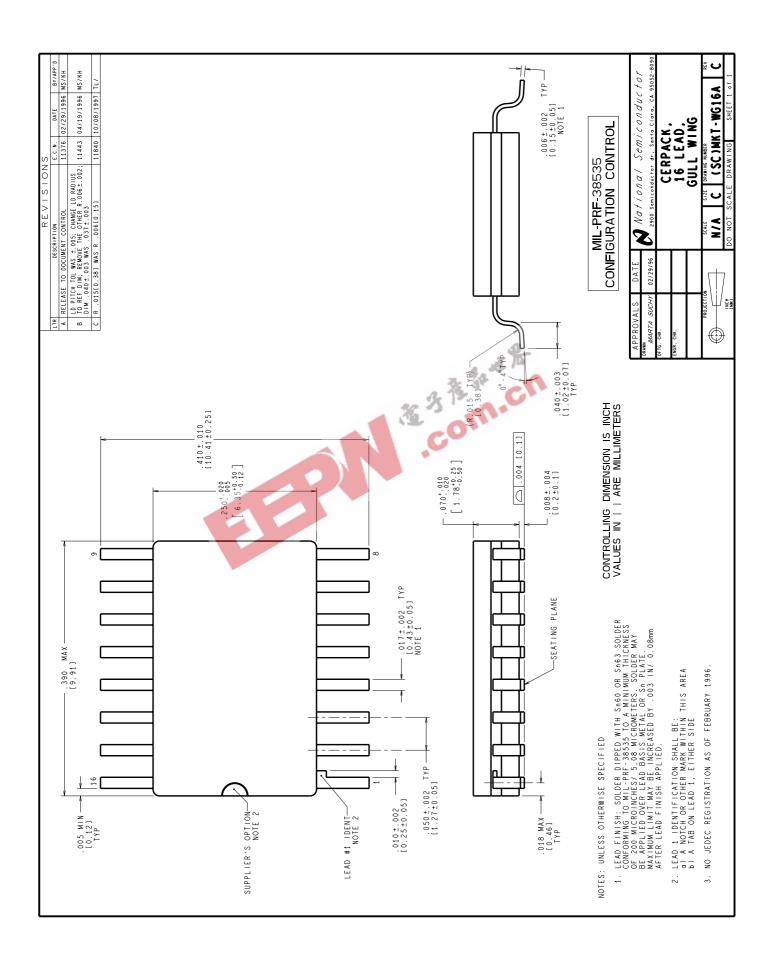












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Revision History

Rev	ECN #	Rel Date	Originator	Changes
0A0	M0000588	10/08/99	Barbara Lopez	Initial Release of: MNLM2940-12-X Rev 0A0. Added note for power dissipation and reference to thermal resistance for Aluminum Nitride package.
1A1	M0003226	10/08/99		Update MDS: MNLM2940-12-X, Rev. 0A0 to MNLM2940-12-X, Rev. 1A1. Moved reference to Controlling Document to Feature Section. Added Graphic's, reference to WG Pkg to Main Table and Absolute Section and also Package Weight heading. Changed Vdo, Io = 100mA, Max. condition for subgroup 1 from 150mV to 200mV and subgroup 2 from 200mV to 300mV.

